



Appl. No. : 10/690,215
Filed : October 20, 2003

AMENDMENTS TO THE SPECIFICATION

Please amend the title from "Method for the Deposition of Silicon Nitride Films" to
"Reactor Precoating for Reduced Stress and Uniform CVD"

Please replace paragraph 0025 with the following paragraph:

[0025] In light of the present disclosure, one of skill in the art will recognize that ammonia need not be the only chemical used in both or either of the deposition steps. Preferably, however, only inorganic reactants are used in the pre-coating step. Alternative nitrogen sources can be selected from the group consisting of: $(\text{H}_3\text{Si})_3\text{N}$ (trisilylamine), ammonia, atomic nitrogen, hydrazine (H_2N_2)(H_4N_2), and hydrazoic acid (HN_3). In another embodiment, nitric oxide is used as a source of nitrogen. In the illustrated embodiment, ammonia is used in both of the deposition steps.